

N-Channel Enhancement Mode MOSFET

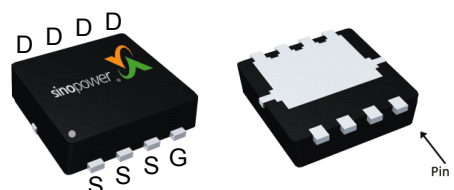
Features

- 30V/18A
 $R_{DS(ON)} = 22m\Omega(max.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 32m\Omega(max.) @ V_{GS} = 4.5V$
- 100% UIS + R_g Tested
- ESD Protection
- Reliable and Rugged
- Lead Free and Green Devices Available
 (RoHS Compliant)

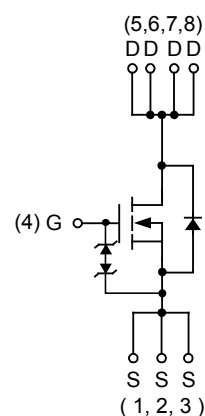
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

Pin Description



DFN3.3x3.3A-8_EP



N-Channel MOSFET

Ordering and Marking Information

SM3434NS □□□-□□□

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	7	A
I _D	Continuous Drain Current	T _C =25°C	18 ^a	A
		T _C =100°C	12	
I _{DM} ^b	Pulsed Drain Current	T _C =25°C	72	A
P _D	Maximum Power Dissipation	T _C =25°C	14.4	W
		T _C =100°C	5.7	
R _{θJC}	Thermal Resistance-Junction to Case	Steady State	8.7	°C/W
I _D	Continuous Drain Current	T _A =25°C	6.5	A
		T _A =70°C	5.2	
I _{DM} ^b	Pulsed Drain Current	T _A =25°C	26	A
P _D	Maximum Power Dissipation	T _A =25°C	1.6	W
		T _A =70°C	1	
R _{θJA} ^c	Thermal Resistance-Junction to Ambient	t ≤ 10s	45	°C/W
		Steady State	80	
I _{AS} ^d	Avalanche Current, Single pulse	L=0.1mH	10.8	A
E _{AS} ^d	Avalanche Energy, Single pulse	L=0.1mH	5.8	mJ

Note a : Max. continuous current is limited by bonding wire.

Note b : Pulse width is limited by max. junction temperature.

Note c : Surface Mounted on 1in^2 pad area, steady state $t=999\text{s}$.

Note d : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^{\circ}\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

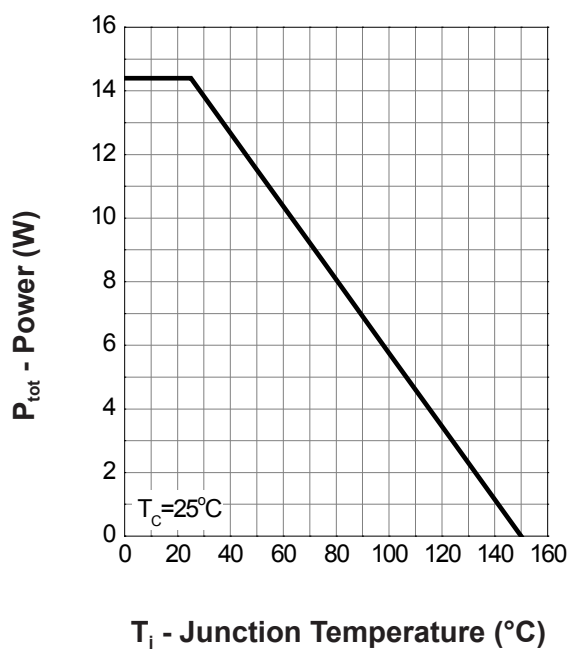
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.5	1.8	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±10	μA
R _{DS(ON)} ^e	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =7A T _J =125°C V _{GS} =4.5V, I _{DS} =5A	- - -	18.4 28.2 24.6	22 - 32	mΩ
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =5A	-	6.5	-	S
Diode Characteristics						
V _{SD} ^e	Diode Forward Voltage	I _{SD} =7A, V _{GS} =0V	-	0.8	1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =7A, dI _{SD} /dt=100A/μs	-	9.5	-	ns
t _a	Charge Time		-	5.6	-	
t _b	Discharge Time		-	4	-	
Q _{rr}	Reverse Recovery Charge		-	4.3	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	3	6	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	330	429	pF
C _{oss}	Output Capacitance		-	57	-	
C _{rss}	Reverse Transfer Capacitance		-	35	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	6.6	12	ns
t _r	Turn-on Rise Time		-	10	18	
t _{d(OFF)}	Turn-off Delay Time		-	15	27	
t _f	Turn-off Fall Time		-	3.3	6	
Gate Charge Characteristics ^f						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =7A	-	7.2	10.1	nC
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =7A	-	3.4	-	
Q _{gth}	Threshold Gate Charge		-	0.6	-	
Q _{gs}	Gate-Source Charge		-	1.1	-	
Q _{gd}	Gate-Drain Charge		-	1.4	-	

Note e : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

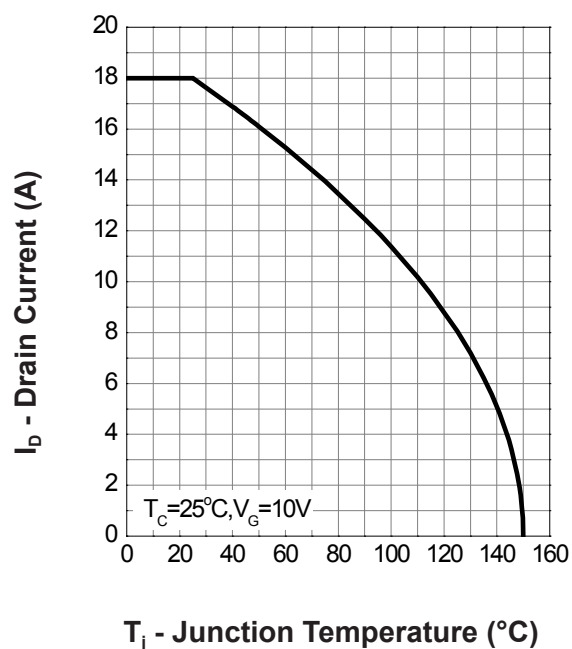
Note f : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

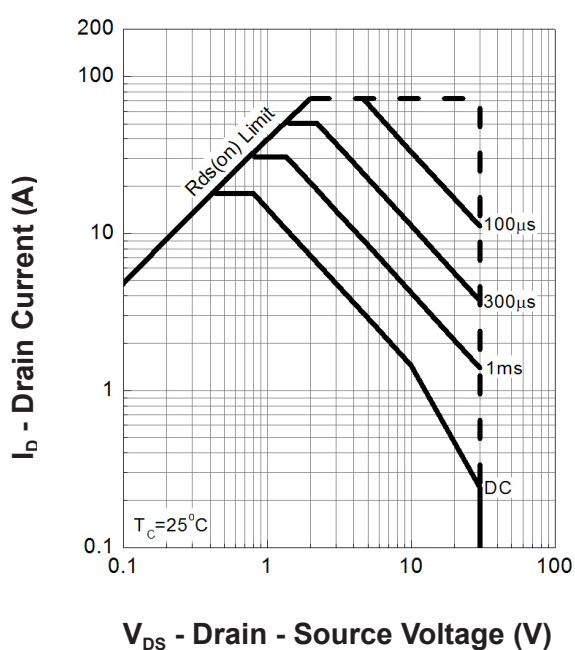
Power Dissipation



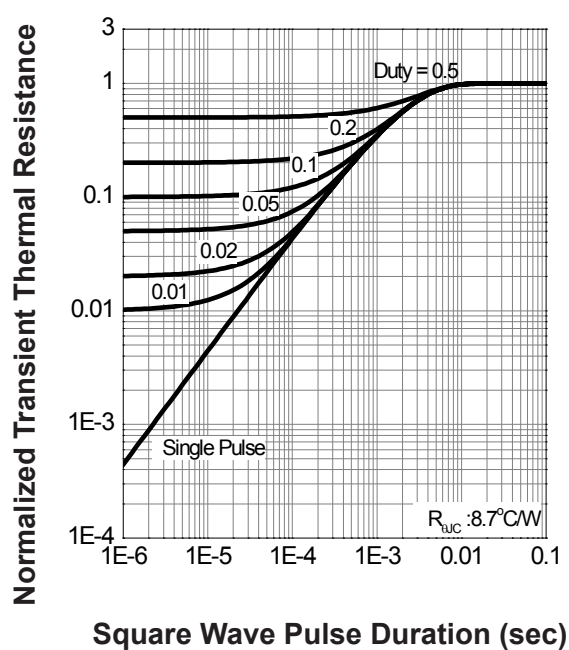
Drain Current



Safe Operation Area

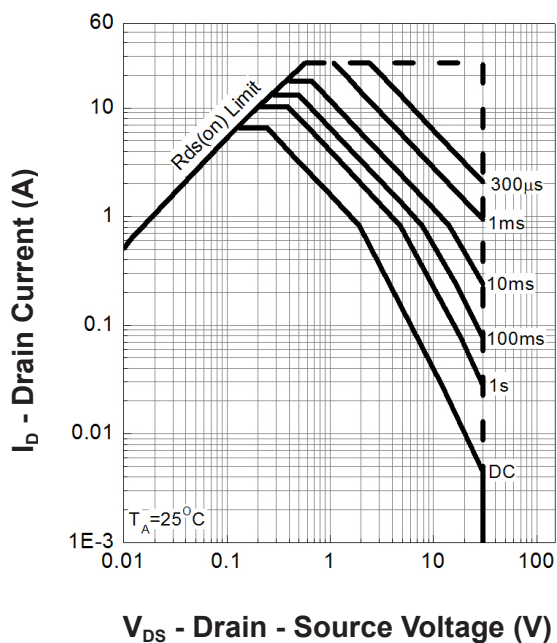


Thermal Transient Impedance

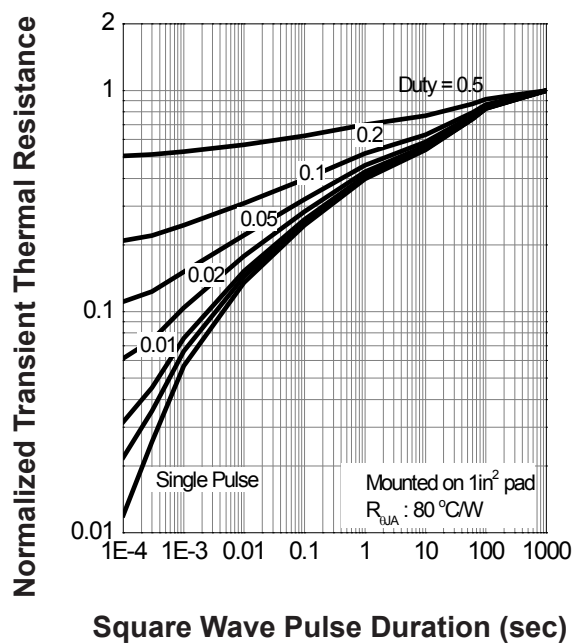


Typical Operating Characteristics(Cont.)

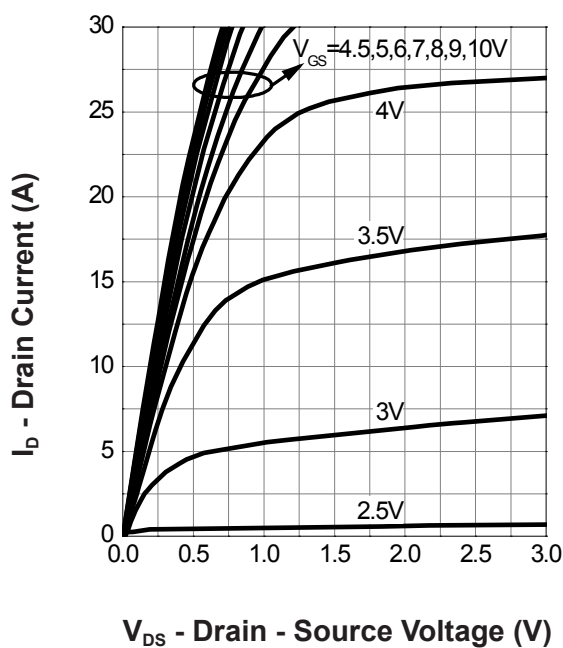
Safe Operation Area



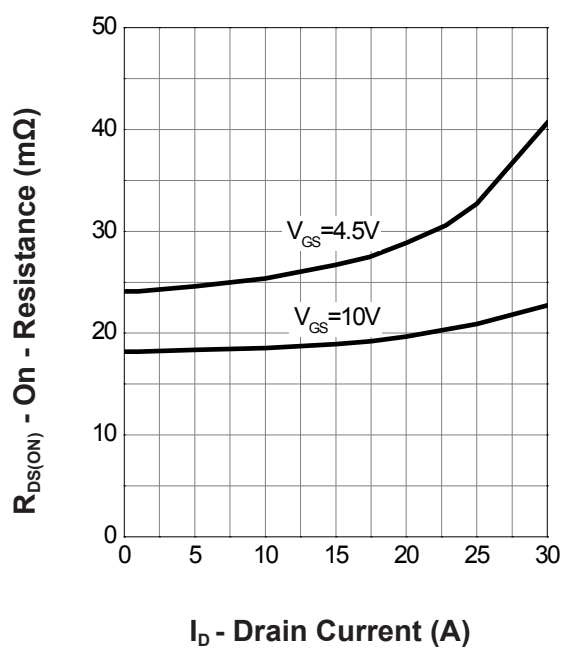
Thermal Transient Impedance



Output Characteristics

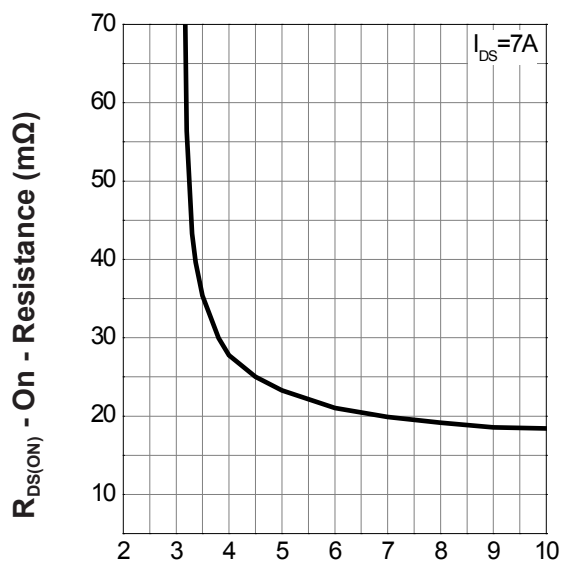


Drain-Source On Resistance

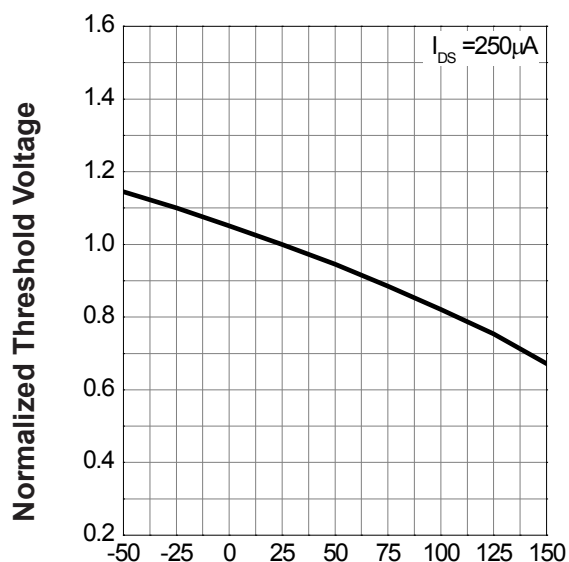


Typical Operating Characteristics(Cont.)

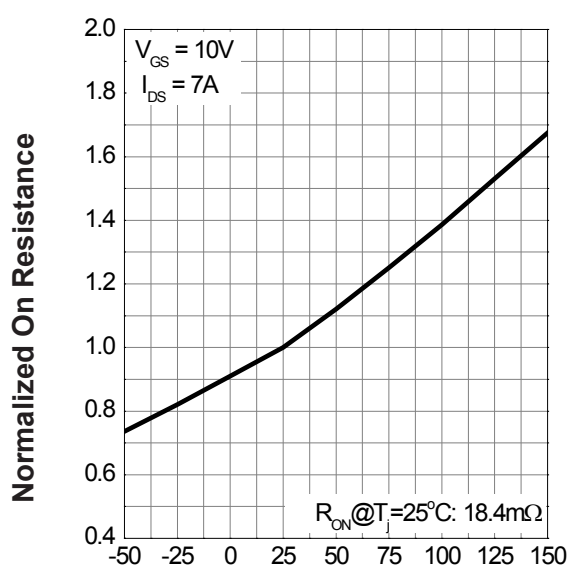
Gate-Source On Resistance

 V_{GS} - Gate - Source Voltage (V)

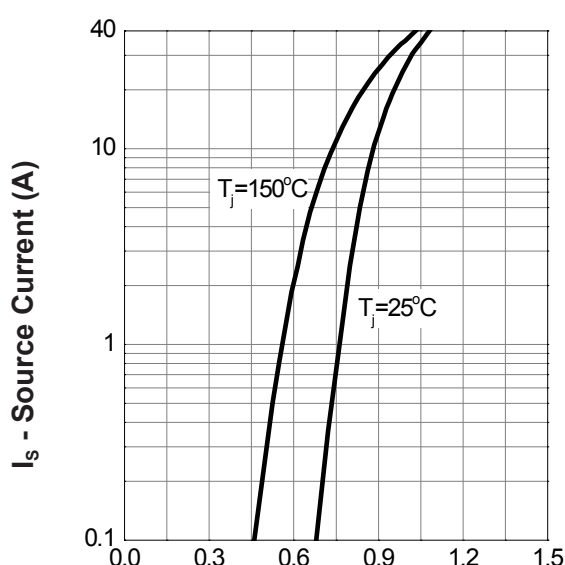
Gate Threshold Voltage

 T_j - Junction Temperature (°C)

Drain-Source On Resistance

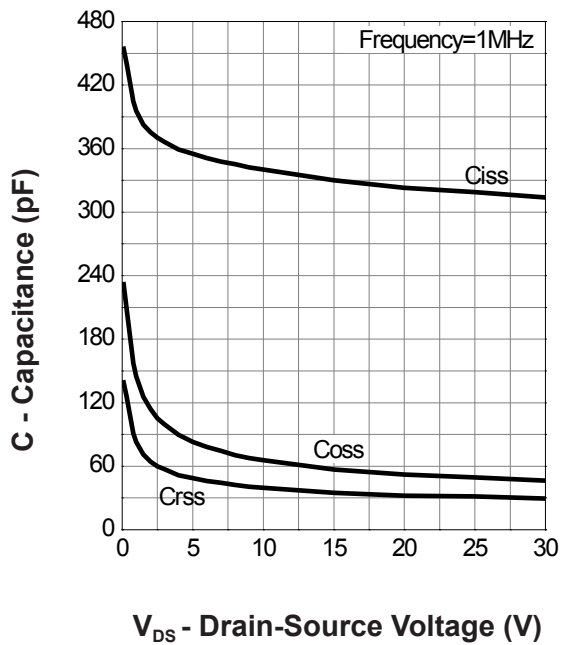
 T_j - Junction Temperature (°C)

Source-Drain Diode Forward

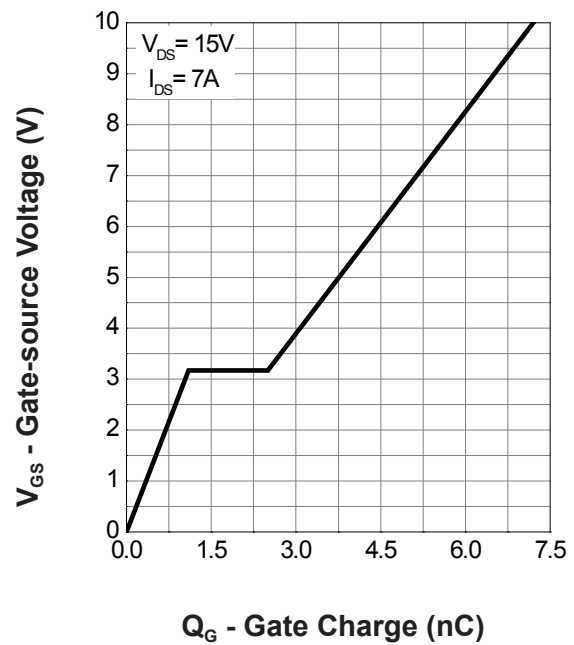
 V_{SD} - Source - Drain Voltage (V)

Typical Operating Characteristics(Cont.)

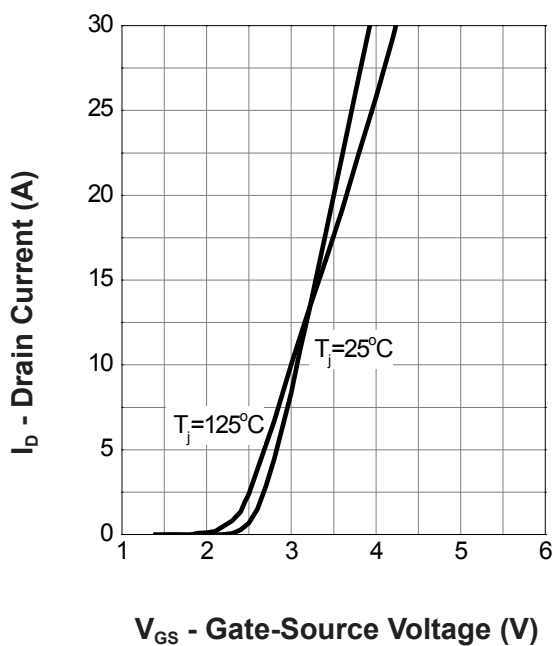
Capacitance



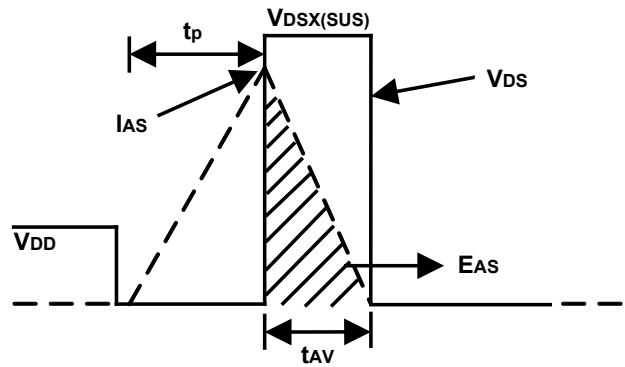
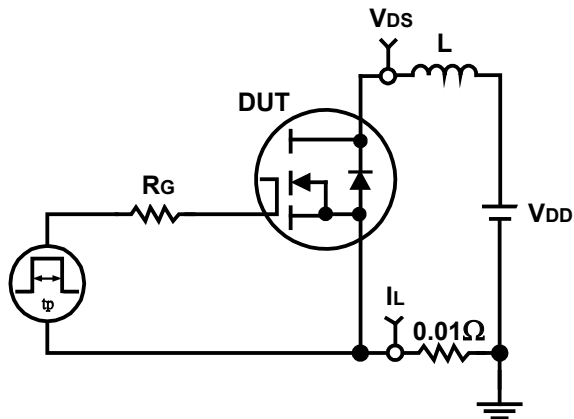
Gate Charge



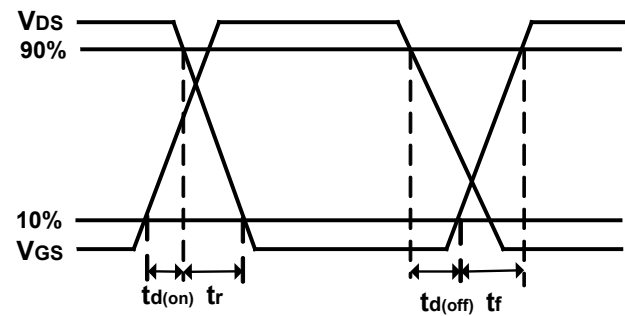
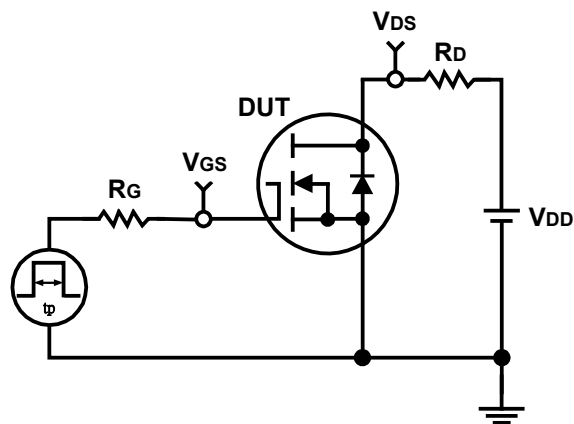
Transfer Characteristics



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



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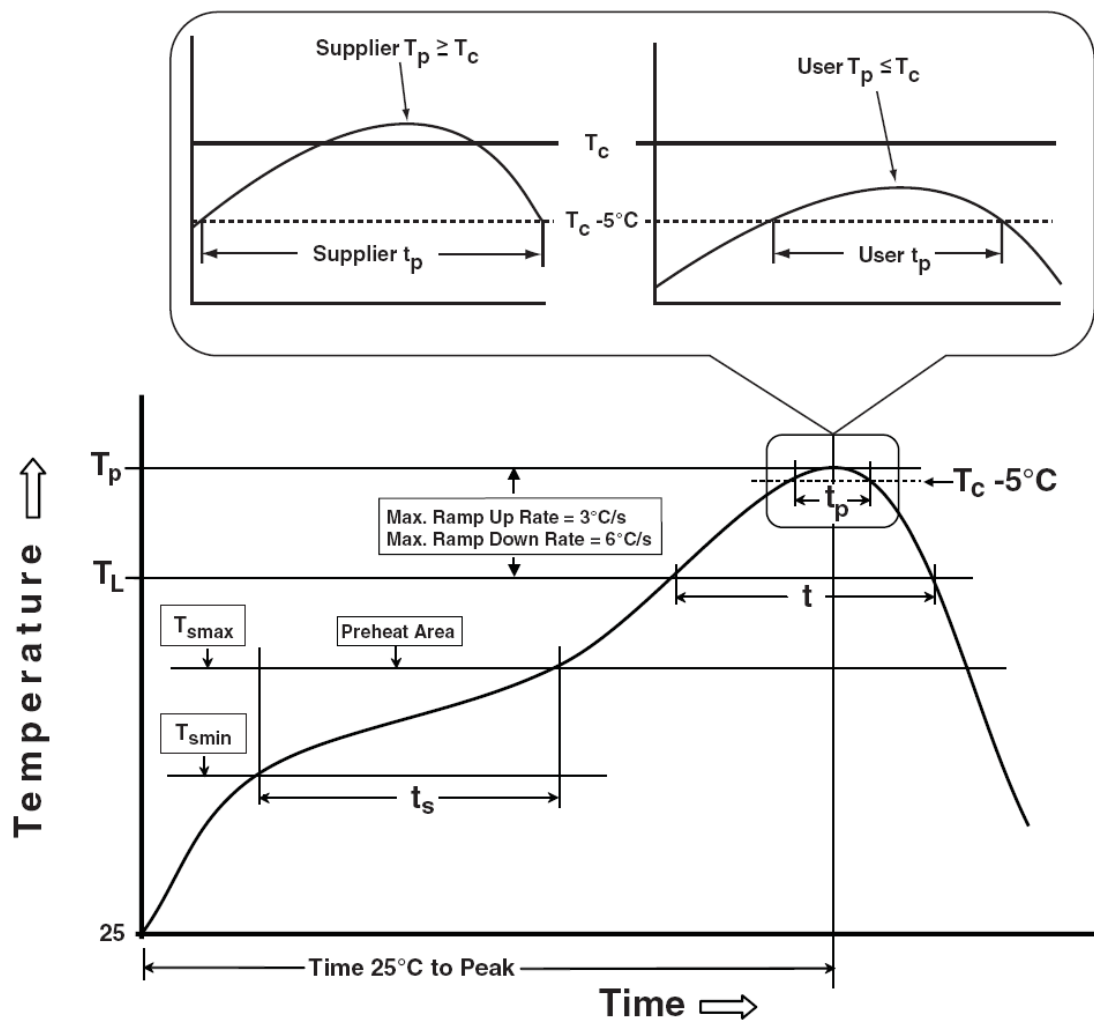
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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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